

## **Corner Free Structure of a Nonvolatile Memory**

### **ABSTRACT OF THE INVENTION**

5           A corner free structure of a nonvolatile memory is disclosed in this present invention. The key aspect of this present invention is employing a corner free structure for isolating a trench isolation device and a nonvolatile memory, and thus the reliability of the above-mentioned nonvolatile memory is improved. Furthermore, based on  
10 the definition of coupling ratio, as a result of the above-cited corner free structure, the effective channel area of the nonvolatile memory is modified, and thus the nonvolatile memory according to this present invention can achieve higher efficiency than the nonvolatile memory in the prior art. Therefore, this invention can not only improve the  
15 reliability of a nonvolatile memory, but also advance the efficiency of the nonvolatile memory.